

NEW COMPLIMENTARY EOS/ESD ASSOCIATION INC. ONLINE SEMINAR

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November 29 at 11:00 AM Eastern Time

An Overview of Design and Reliability of Gallium Nitride HEMT Power Devices

Instructor: Prof. Mayank Srivastava, IISc, Bangalore

Gallium Nitride Based Power electronic devices are projected to cross \$1B mark by 2022 and \$5B mark by 2025 with a market dominance in medium voltage segment. However, the question is would GaN enjoy a similar development roadmap that Si power devices have enjoyed and can it leverage learning/know-how developed from Si power device technology. If not, what is required to be addressed at this stage of technology development? This talk will first give a brief review of techno-commercial aspects of GaN HEMT technology and design aspects. The talk will then address critical reliability-aware design is for GaN HEMT technology while highlighting some new learnings we have acquired both regarding long term reliability of commercial GaN devices, as well as SOA like short time device reliability of in-house developed GaN devices. Finally, TCAD methodology and TCAD based design approach for GaN HEMT technology will be introduced.

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Instructions to access the training will be sent by email prior to November 29th

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